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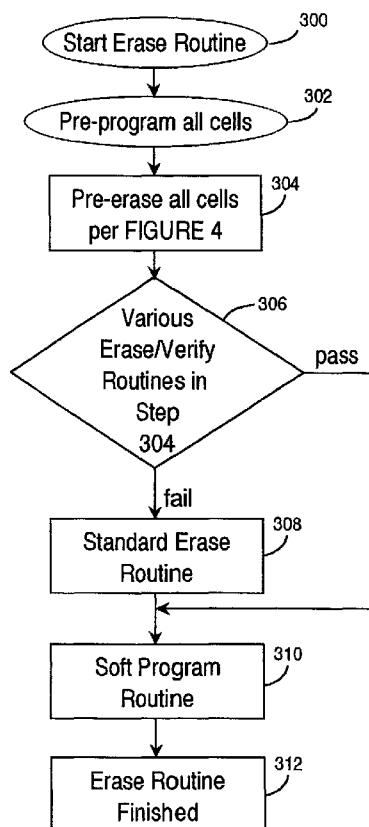
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(54) Title: METHOD OF ERASING A FLASHING MEMORY USING A PRE-ERASING STEP

(57) Abstract: A method of erasing a sector of flash memory cells wherein a first set of preset pre-erase voltages is applied to the sector of flash memory cells (402). After the first set of preset pre-erase voltages is applied it is determined if another set of preset pre-erase voltages is to be applied to the sector of flash memory cells (410). If another set of preset pre-erase voltages is not to be applied, a standard erase routine is applied to the sector (411).



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